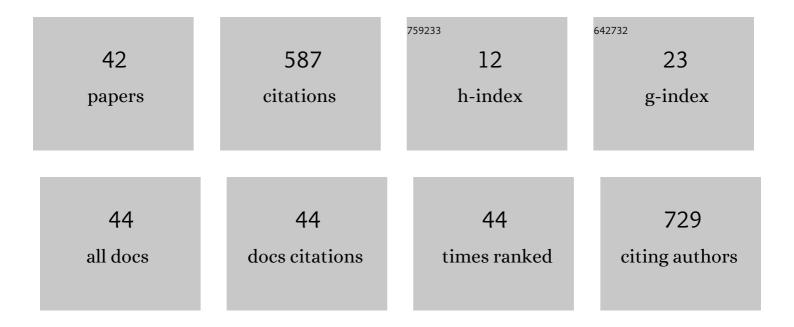
Ryota Negishi

List of Publications by Year in descending order

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RVOTA NECISHI

#	Article	IF	CITATIONS
1	Band-like transport in highly crystalline graphene films from defective graphene oxides. Scientific Reports, 2016, 6, 28936.	3.3	68
2	Ionic-Electronic Conductor Nanostructures: Template-Confined Growth and Nonlinear Electrical Transport. Small, 2005, 1, 971-975.	10.0	62
3	Fabrication of nanoscale gaps using a combination of self-assembled molecular and electron beam lithographic techniques. Applied Physics Letters, 2006, 88, 223111.	3.3	60
4	Layer-by-layer growth of graphene layers on graphene substrates by chemical vapor deposition. Thin Solid Films, 2011, 519, 6447-6452.	1.8	53
5	Turbostratic multilayer graphene synthesis on CVD graphene template toward improving electrical performance. Japanese Journal of Applied Physics, 2019, 58, SIIB04.	1.5	35
6	I-V characteristics of single electron tunneling from symmetric and asymmetric double-barrier tunneling junctions. Applied Physics Letters, 2007, 90, 223112.	3.3	32
7	Extraordinary suppression of carrier scattering in large area graphene oxide films. Applied Physics Letters, 2014, 105, .	3.3	28
8	Size-dependent single electron tunneling effect in Au nanoparticles. Surface Science, 2007, 601, 3907-3911.	1.9	25
9	Method for Controlling Electrical Properties of Single-Layer Graphene Nanoribbons via Adsorbed Planar Molecular Nanoparticles. Scientific Reports, 2015, 5, 12341.	3.3	21
10	Synthesis of very narrow multilayer graphene nanoribbon with turbostratic stacking. Applied Physics Letters, 2017, 110, .	3.3	13
11	Turbostratic Stacking Effect in Multilayer Graphene on the Electrical Transport Properties. Physica Status Solidi (B): Basic Research, 2020, 257, 1900437.	1.5	13
12	The fabrication and single electron transport of Au nano-particles placed between Nb nanogap electrodes. Nanotechnology, 2010, 21, 225301.	2.6	12
13	Thickness Control of Graphene Overlayer via Layer-by-Layer Growth on Graphene Templates by Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2011, 50, 06GE04.	1.5	12
14	Carrier Transport Properties of the Field Effect Transistors with Graphene Channel Prepared by Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2012, 51, 06FD03.	1.5	12
15	Carrier Transport Properties of the Field Effect Transistors with Graphene Channel Prepared by Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2012, 51, 06FD03.	1.5	12
16	Study of photoelectron spectroscopy from extremely uniform Si nanoislands on Si(111) 7×7 substrate. Journal of Applied Physics, 2004, 96, 5013-5016.	2.5	11
17	Local structure and electronic state of a nanoscale Si island on Si()-7×7 substrate. Surface Science, 2002, 507-510, 582-587.	1.9	10
18	Interrelations between the local electronic states and the atomic structures in the Si nanoscale island on Si(111)-(7×7) surface. Journal of Applied Physics, 2003, 93, 4824-4830.	2.5	10

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#	Article	IF	CITATIONS
19	Strain and electronic structure of Ge nanoislands on Si(111)-7×7surface. Physical Review B, 2005, 72, .	3.2	10
20	Biosensor response from target molecules with inhomogeneous charge localization. Journal of Applied Physics, 2018, 124, 064502.	2.5	9
21	Diameter dependence of longitudinal unzipping of single-walled carbon nanotube to obtain graphene nanoribbon. Japanese Journal of Applied Physics, 2017, 56, 06GG12.	1.5	8
22	Strain induced modification of quasi-two-dimensional electron gas state on â^š3×â^š3-Ag structure. Journal of Applied Physics, 2010, 107, 084317.	2.5	7
23	Improving sensor response using reduced graphene oxide film transistor biosensor by controlling the adsorption of pyrene as an anchor molecule. Japanese Journal of Applied Physics, 2017, 56, 06GE04.	1.5	7
24	Modification of electronic states of â^š3×â^š3-Ag structure by strained Ge/Si(111) substrate. Journal of Applied Physics, 2009, 106, .	2.5	6
25	Thickness Control of Graphene Overlayer via Layer-by-Layer Growth on Graphene Templates by Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2011, 50, 06GE04.	1.5	6
26	Fabrication of uniform Au silicide islands on the Si(111)-(7×7) substrate. Surface Science, 2006, 600, 1125-1128.	1.9	5
27	Influence of nanoparticle size to the electrical properties of naphthalenediimide on single-walled carbon nanotube wiring. Nanotechnology, 2012, 23, 215701.	2.6	5
28	Surface roughening induced by a characteristic surface structure of a Si film grown on Si(111). Surface Science, 2001, 481, 67-77.	1.9	4
29	Electronic structures of dangling-bond states on the Si nanoisland and the Si(111) 7×7 substrate. Journal of Applied Physics, 2005, 98, 063712.	2.5	4
30	Fabrication of Nanogap Electrodes by the Molecular Lithography Technique. Japanese Journal of Applied Physics, 2011, 50, 035204.	1,5	4
31	Effect of a protective layer on a carbon nanotube thin film channel in a biosensor device. Japanese Journal of Applied Physics, 2019, 58, SIIB14.	1.5	4
32	Scanning probe analysis of twisted graphene grown on a graphene/silicon carbide template. Nanotechnology, 2022, 33, 155603.	2.6	4
33	Investigation of surface potentials in reduced graphene oxide flake by Kelvin probe force microscopy. Japanese Journal of Applied Physics, 2018, 57, 06HD02.	1.5	3
34	Crossover point of the field effect transistor and interconnect applications in turbostratic multilayer graphene nanoribbon channel. Scientific Reports, 2021, 11, 10206.	3.3	3
35	Nucleation of polycrystalline layer induced by formation of 30° partial dislocation during Si/Si() growth. Surface Science, 2002, 505, 225-233.	1.9	2
36	Turbostratic Stacking Effect in Multilayer Graphene on the Electrical Transport Properties. Physica Status Solidi (B): Basic Research, 2020, 257, 2070015.	1.5	2

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#	Article	IF	CITATIONS
37	Growth of metallic Au adsorbed islands on the Si(111)-(7 × 7) substrate. Journal of Physics: Conference Series, 2007, 61, 1056-1060.	0.4	1
38	Neuromorphic switching behavior in multi-stacking composed of Pt/graphene oxide/Ag ₂ S/Ag. Japanese Journal of Applied Physics, 2019, 58, SIID08.	1.5	1
39	LOCAL ELECTRONIC STATES ON TWO-DIMENSIONAL NANOSCALE ISLAND OF Si AND Ge FABRICATED ON Si(111) 7 × 7 SUBSTRATE. International Journal of Nanoscience, 2009, 08, 595-603.	0.7	Ο
40	Fabrication and Developments of Nano-gap Electrode using Self-assembled Molecular Lithography. Journal of the Vacuum Society of Japan, 2012, 55, 333-340.	0.3	0
41	Strain induced intermixing of Ge atoms in Si epitaxial layer on Ge(111). Journal of Applied Physics, 2013, 113, 073511.	2.5	0
42	Fine Structure and Local Electronic States on Two-dimensional Nanoscale Islands of Si and Ge. Journal of the Vacuum Society of Japan, 2008, 51, 291-297.	0.3	0